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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SCRs

.5 Amp, Planar

FEATURES

- Voltage Ratings: to 400V
- Maximum Gate Trigger Current: 200μA
- Hermetically Sealed TO-18 Metal Can
- Planar Passivated Construction

DESCRIPTION

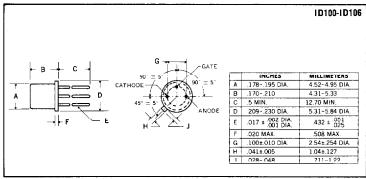
This Data Sheet describes Microsemi's line of hermetically sealed industrial SCRs designed for low-voltage, low-current sensing application. The ID100 Series is packaged in a TO-18 metal case with Microsemi's unique oxide passivated junctions, offering the highest degree of reliability and parameter stability for any device in its price range.

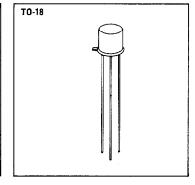
Typical applications include lamp driving, relay driving, sensor, pulse-generating and timing circuits.

ABSOLUTE MAXIMUM RATINGS

	ID100	ID101	ID102	ID103	10104	ID105	ID106
Repetitive Peak Off-State Voltage, VDRM	30V	60V	100V	150V	200V	300V	400V
Repetitive Peak Reverse Voltage, VRRM	30V	60V	100V	150V	200V	300V	400V
On-State Current, I _T							
75°C Ambient				250mA			
100°C Case				0.5A			
Repetitive Peak On-State Current, ITRM				6A			
Peak One Cycle Surge (Non-Rep.) On-State Curren	nt, I _{rsm}			up to 30A			
Peak Gate Current, I _{GM} Average Gate Current, I _{G(AV)}				250mA			
Average Gate Current, IG(AV)				25mA			
Reverse Gate Voltage, V _{GR}				6V			
Storage Temperature Range			—6	5°C to +150°	C		
Operating Temperature Range			6	5°C to +125°	C		

MECHANICAL SPECIFICATIONS





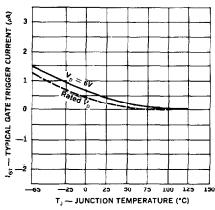


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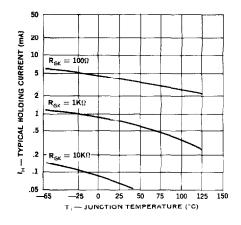
Test	Symbol	Min.	Typical	Max.	Units	Test Conditions
Off-State Current	I _{DRM}		5.0 10.0	50 100	μ Α μ Α	$V_{DRM} = Rating, R_{GK} = 1K, T = 125^{\circ}C, ID100-ID104$ $V_{DRM} = Rating, R_{GK} = 1K, T = 125^{\circ}C, ID105-ID106$
Reversing Current	I _{RRM}	_	10 15	50 100	μ Α μ Α	$V_{RRM} = Rating, R_{GK} = 1K, T = 125^{\circ}C, ID100-ID104$ $V_{RRM} = Rating, R_{GK} = 1K, T = 125^{\circ}C, ID105-ID106$
Gate Trigger Current	I _{GT}	_	5.0 —	200 500	μ Α μ Α	$V_D = 5V, R_{GS} = 10K$ $V_D = 5V, R_{GS} = 10K, T = -40^{\circ}C$
Gate Trigger Voltage	V _{G1}	0.4 0.10	0.55	0.8 1.0	V V V	$V_D = 5V$, $R_{GS} = 100\Omega$ $V_D = 5V$, $R_{GS} = 100\Omega$, $T = 40^{\circ}$ C $V_D = 5V$, $R_{GS} = 100\Omega$, $T = 125^{\circ}$ C
Peak On-State Voltage	V _{TM}	_	_	1.7	٧	I _{TM} = 1 Amp Pulse
Holding Current	I _H		1.0	5.0 10.0	mA mA	$R_{GK} = 1K$ $R_{GK} = 1K$, $T = -40^{\circ}C$
Turn-on Time	t _{on}		0.5	_	μS	$I_{G} = 10 \text{mA}, I_{T} = 1 \text{A}, V_{D} = 30 \text{V}$
Circuit Commutated Turn-off Time	t _q		8.0 15.0	_	μ\$ μ s	$I_7 = I_R = 1A$, $R_{GK} = 1K$, $ID100-ID104$ $I_7 - I_R - 1A$, $R_{GK} = 1K$, $ID105-ID106$

Note: Blocking voltage ratings apply over the full operating temperature range, provided the gate is connected to the cathode through a resistor, 1000 ohms or smaller, or other adequate bias is used.

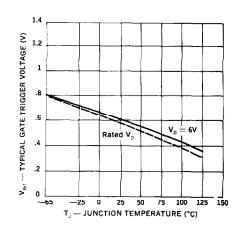
Gate Trigger Current vs. Junction Temp.



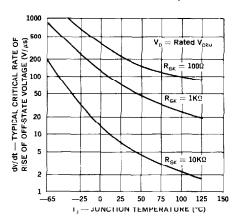
Holding Current vs. Junction Temp.



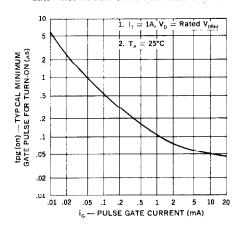
Gate Trigger Voltage vs. Junction Temp.

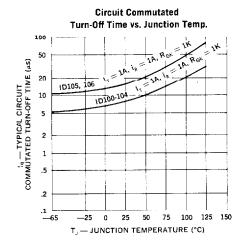


dv/dt vs. Junction Temp.

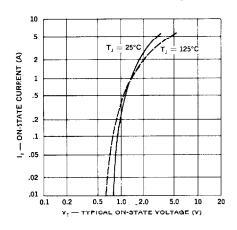


Gate Pulse for Turn-On vs. Pulse Gate Current





Gurrent vs. On State Voltage



Current vs. Power Dissipation

